



Silicon Carbide Dual Schottky Power Rectifier 10A, 600V

ORDERABLE PART NUMBERS			
	MSiCSN10060CC	MSiCSN10060CA	MSiCSN10060D
Configuration	Common Cathode	Common Anode	Doubler

DESCRIPTION

These dual 600 V rated SiC Schottky rectifiers are in a hermetically sealed package with options for common cathode, common anode, and doubler configurations. They offer very fast switching capabilities with greater efficiency at higher operating temperatures compared to existing ultrafast silicon rectifiers.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

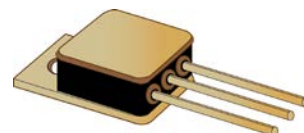
- TO-257 package
- Lightweight
- Hermetically sealed package
- Internal metallurgical bonds
- High temperature (T_J) +175 °C
- Zero reverse recovery current
- Temperature independent switching behavior
- Very fast switching compared to fast or ultrafast rectifiers
- Positive V_F temperature coefficient (parallel devices for higher currents)
- RoHS compliant versions are available

APPLICATIONS / BENEFITS

- Schottky barrier diode for military, space and other high reliability applications
- Switching power supplies or other applications requiring extremely fast switching and essentially no switching losses
- High forward surge capability
- High reverse voltage capability with very fast switching.
- Inherently radiation hard >100 krad as described in Microsemi [MicroNote 050](#)


MAXIMUM RATINGS @ $T_C = +25\text{ °C}$ unless otherwise noted.


Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-65 to +175	°C
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.6	°C/W
Working Peak Reverse Voltage	V_{RWM}	600	V
Non-Repetitive Peak Inverse Voltage	V_{RSM}	600	V
DC Blocking Voltage	V_{DC}	600	V
Average DC Output Current @ 25 °C	I_O	10	A
Non-Repetitive Sinusoidal Surge Current @ $t_p = 8.3\text{ ms}$, half sinewave, $I_O = 0$; $V_{RM} = 0$	I_{FSM}	50	A




TO-257 Package

Also available in:

Dual U3 package
(surface mount)
 [MSiCSS10060CC](#)

U4 package
(surface mount)
 [MSiCSS10060](#)

TO-257 package
(leaded)
 [MSiCSN10060](#)

MSC – Lawrence

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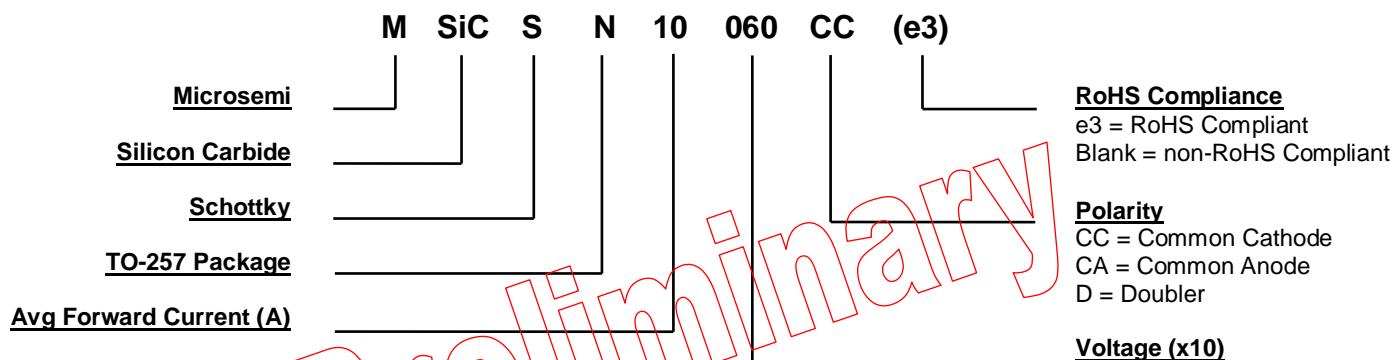
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www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Nickel plated copper base & 1020 steel frame
- TERMINALS: Solder dipped copper cored 52 alloy or RoHS compliant matte-tin plating
- MARKING: Alpha numeric
- POLARITY: See [schematic](#) on last page
- WEIGHT: Approximately 3.43 grams
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

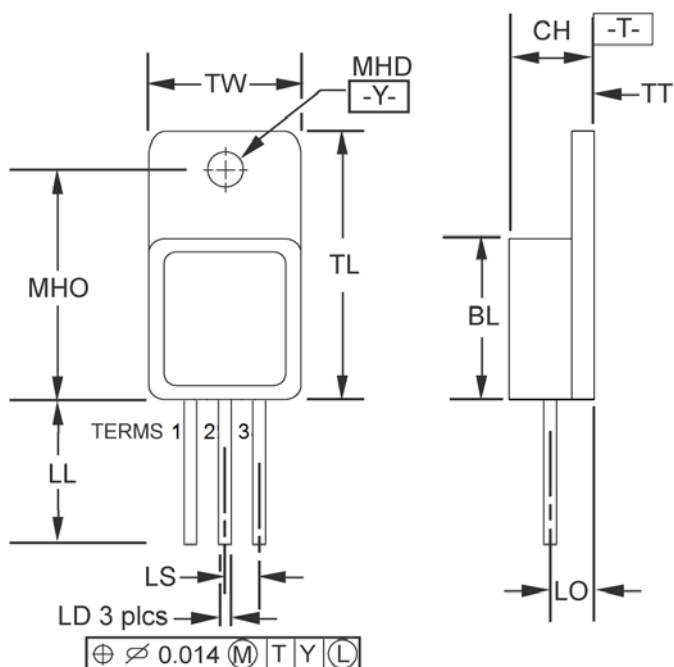
Symbol	Definition
C_J	Junction Capacitance: The junction capacitance in pF at a specified frequency (typically 1 MHz) and specified voltage.
I_F	Forward Current: The forward current dc value, no alternating component.
I_R	Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.
T_J	Junction Temperature: The temperature of a semiconductor junction.
V_F	Forward Voltage: The forward voltage the device will exhibit at a specified current (typically shown as maximum value).
V_R	Reverse Voltage: The reverse voltage dc value, no alternating component.

ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$ unless otherwise noted

Parameters / Test Conditions	Symbol	Min.	Max.	Typ.	Unit
Forward Voltage* $I_F = 1\text{ A}$, $T_J = 25^\circ\text{C}$ $I_F = 2.5\text{ A}$, $T_J = 25^\circ\text{C}$ $I_F = 5.0\text{ A}$, $T_J = 25^\circ\text{C}$ $I_F = 10.0\text{ A}$, $T_J = 25^\circ\text{C}$	V_F		1.1 1.2 1.4 1.8		V
Reverse Current $V_R = 600\text{ V}$, $T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$, $T_J = 175^\circ\text{C}$	I_R		50 100		μA
Junction Capacitance $V_R = 0\text{ V}$ $f = 1\text{ MHz}$	C_J			550	pF

* Pulse test: Pulse width 300 μsec , duty cycle 2%.

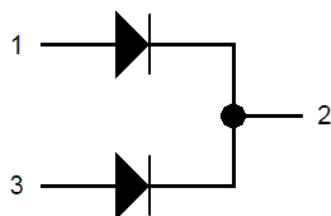
Preliminary

PACKAGE DIMENSIONS


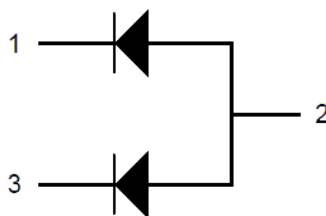
Ltr	Dimensions			
	Inch		Millimeters	
	Min	Min	Min	Max
BL	0.410	0.430	10.41	10.92
CH	0.190	0.200	4.83	5.08
LD	0.025	0.035	0.64	0.89
LL	0.505	0.595	12.82	15.11
LO	0.120 BSC		3.05 BSC	
LS	0.100 BSC		2.54 BSC	
MHD	0.140	0.150	3.56	3.81
MHO	0.527	0.537	13.39	13.64
TL	0.645	0.665	16.38	16.89
TT	0.035	0.045	0.89	1.14
TW	0.410	0.420	10.41	10.67
TERM 1	SEE SCHEMATIC			
TERM 2	SEE SCHEMATIC			
TERM 3	SEE SCHEMATIC			

NOTES:

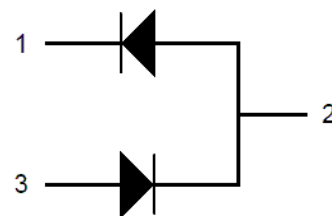
1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Glass meniscus included in dimension TL and BL.

SCHEMATIC
CC - COMMON CATHODE


TERM 1 = ANODE
TERM 2 = CATHODE
TERM 3 = ANODE

CA - COMMON ANODE


TERM 1 = CATHODE
TERM 2 = ANODE
TERM 3 = CATHODE

D - DOUBLER


TERM 1 = CATHODE
TERM 2 = CENTER TAP
TERM 3 = ANODE